June 2015

SemiHow
Know-How for Semiconductor

HCD65R600S / HCU65R600S

650V N-Channel Super Junction MOSFET

BV_{DSS} = 650 V

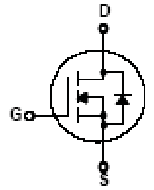
$R_{DS(on)\ typ}$ = 0.54 Ω

I_D = 7.3 A

D-PAK **I-PAK**

HCD65R600S HCU65R600S

1.Gate 2. Drain 3. Source



FEATURES

- ☐ Originative New Design
- ☐ Superior Avalanche Rugged Technology
- ☐ Robust Gate Oxide Technology
- ☐ Very Low Intrinsic Capacitances
- ☐ Excellent Switching Characteristics
- ☐ Unrivalled Gate Charge : 16 nC (Typ.)
- ☐ Extended Safe Operating Area
- ☐ Lower $R_{DS(ON)}$: 0.54 Ω (Typ.) @V_{GS}=10V
- ☐ 100% Avalanche Tested

Absolute Maximum Ratings

T_C=25℃ unless otherwise specified

Symbol	Parameter	Value	Units
V_{DSS}	Drain-Source Voltage	650	V
I_D	Drain Current – Continuous (T_C = 25℃)	7.3	A
	Drain Current – Continuous (T_C = 100℃)	4.6	A
I_{DM}	Drain Current – Pulsed (Note 1)	22	A
V_{GS}	Gate-Source Voltage	±20	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	150	mJ
I_{AR}	Avalanche Current (Note 1)	2.0	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	0.5	mJ
dv/dt	Peak Diode Recovery dv/dt	15	V/ns
P_D	Power Dissipation (T_A = 25℃)*	2.5	W
	Power Dissipation (T_C = 25℃)	69	W
	- Derate above 25℃	0.55	W/℃
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	℃
T_L	Maximum lead temperature for soldering purposes, 1/8” from case for 5 seconds	300	℃

Thermal Resistance Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	1.8	℃/W
$R_{\theta JA}$	Junction-to-Ambient*	--	50	
$R_{\theta JA}$	Junction-to-Ambient	--	110	

* When mounted on the minimum pad size recommended (PCB Mount)

Electrical Characteristics T_J=25 °C unless otherwise specified

On Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
V_{GS}	Gate Threshold Voltage	$V_{DS} = V_{GS}$, I_D = 250 ㎂	2.8	--	4.2	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 3.5 A	--	0.54	0.6	Ω

Off Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 ㎂	650	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 650 V, V_{GS} = 0 V	--	--	10	㎂
		V_{DS} = 520 V, T_J = 125℃	--	--	100	㎂
I_{GSS}	Gate-Body Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V	--	--	±100	㎁

Dynamic Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	--	500	--	㎊
C_{oss}	Output Capacitance		--	250	--	㎊
C_{rss}	Reverse Transfer Capacitance		--	7	--	㎊
R_g	Gate Resistance	V_{GS} = 0 V, V_{DS} = 0 V, f = 1MHz	--	4	--	Ω

Switching Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$t_{d(on)}$	Turn-On Time	V_{DS} = 325 V, I_D = 7.3 A, R_G = 25 Ω	--	20	--	㎱
t_r	Turn-On Rise Time		--	20	--	㎱
$t_{d(off)}$	Turn-Off Delay Time		--	60	--	㎱
t_f	Turn-Off Fall Time		--	20	--	㎱
Q_g	Total Gate Charge	V_{DS} = 520 V, I_D = 7.3 A, V_{GS} = 10 V	--	16	--	nC
Q_{gs}	Gate-Source Charge		--	4.0	--	nC
Q_{gd}	Gate-Drain Charge		--	5.5	--	nC

Source-Drain Diode Maximum Ratings and Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
I_S	Continuous Source-Drain Diode Forward Current		--	--	7.3	A
I_{SM}	Pulsed Source-Drain Diode Forward Current		--	--	22	
V_{SD}	Source-Drain Diode Forward Voltage	I_S = 7.3 A, V_{GS} = 0 V	--	--	1.3	V
trr	Reverse Recovery Time	I_S = 3.5 A, V_{GS} = 0 V, di_F/dt = 100 A/μs	--	250	--	㎱
Qrr	Reverse Recovery Charge		--	2	--	uC

Notes :

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. I_{AS}=2A, V_{DD}=50V, R_G=25Ω, Starting T_J =25°C

Typical Characteristics

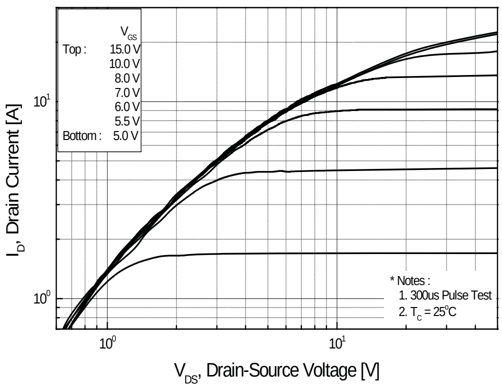


Figure 1. On Region Characteristics

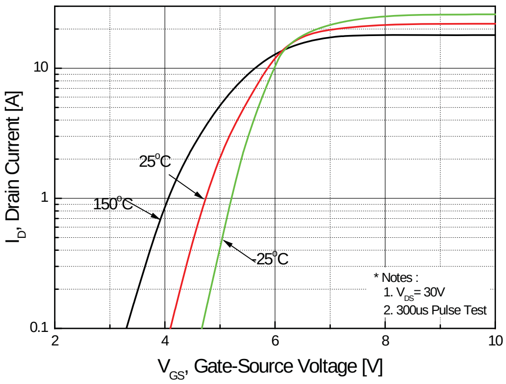


Figure 2. Transfer Characteristics

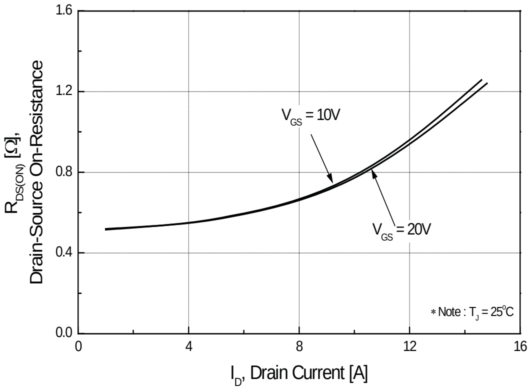


Figure 3. On Resistance Variation vs Drain Current and Gate Voltage

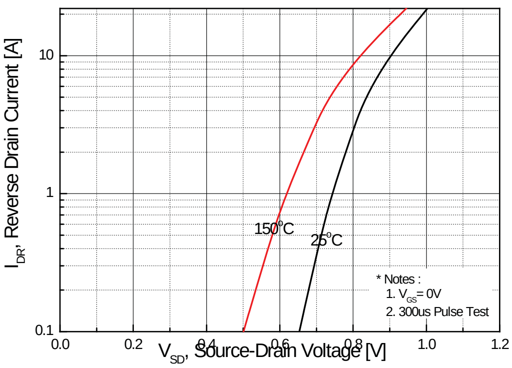


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

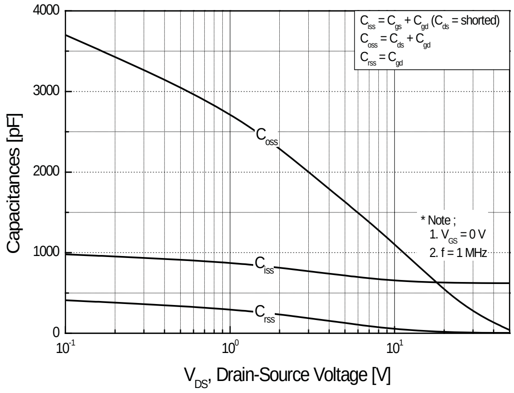


Figure 5. Capacitance Characteristics

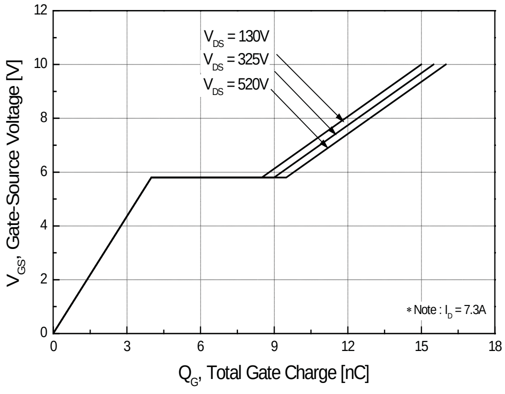


Figure 6. Gate Charge Characteristics

Typical Characteristics (continued)

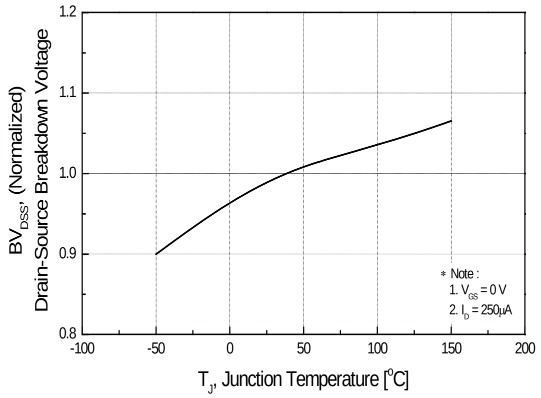


Figure 7. Breakdown Voltage Variation vs Temperature

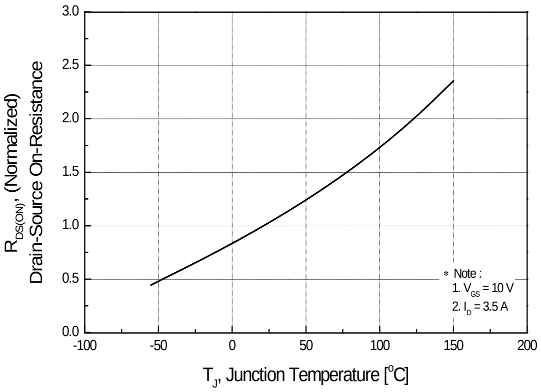


Figure 8. On-Resistance Variation vs Temperature

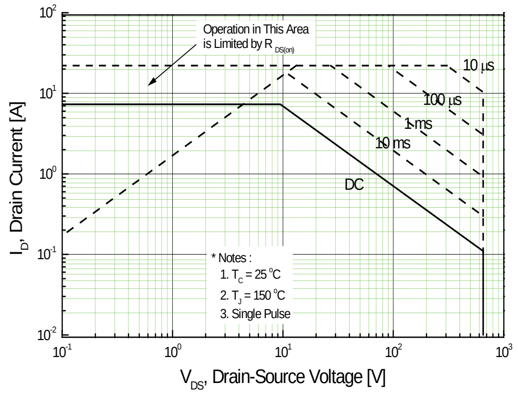


Figure 9. Maximum Safe Operating Area

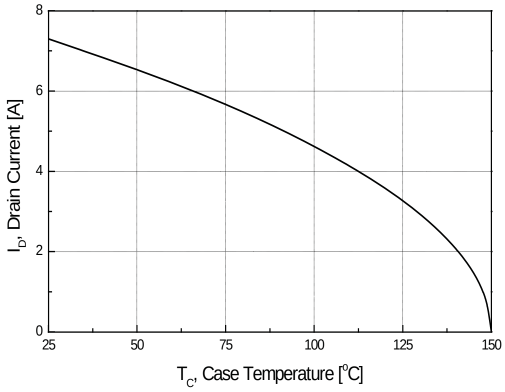


Figure 10. Maximum Drain Current vs Case Temperature

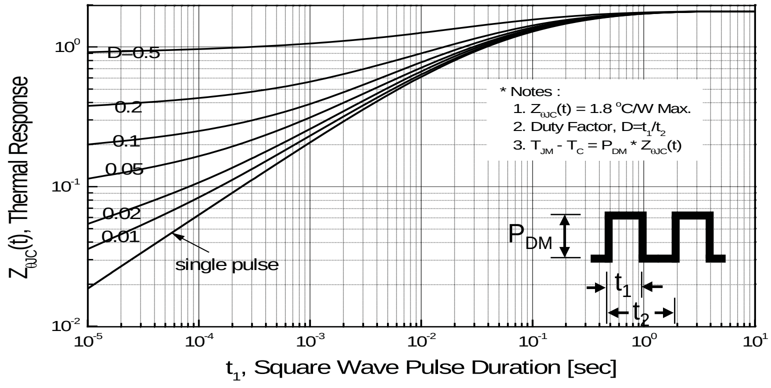


Figure 11. Transient Thermal Response Curve

Fig 12. Gate Charge Test Circuit & Waveform

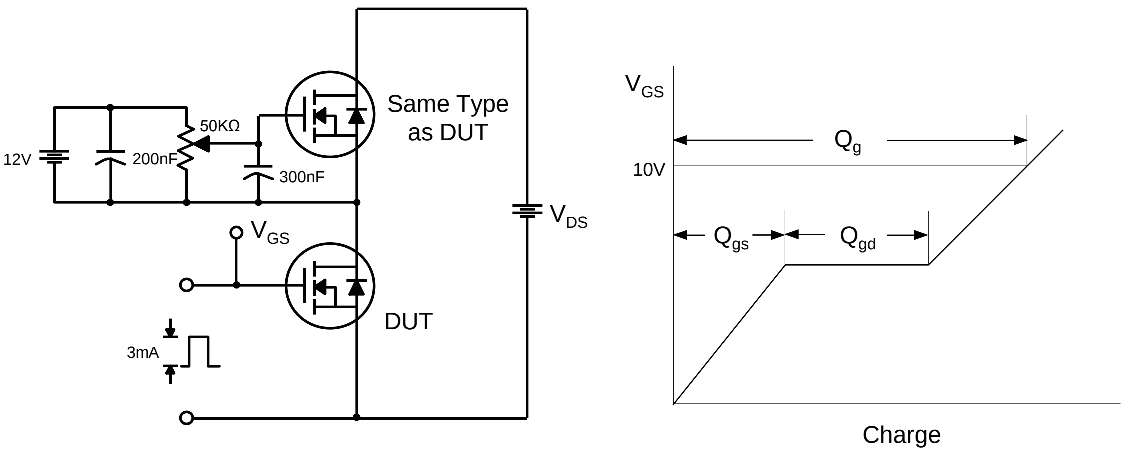


Fig 13. Resistive Switching Test Circuit & Waveforms

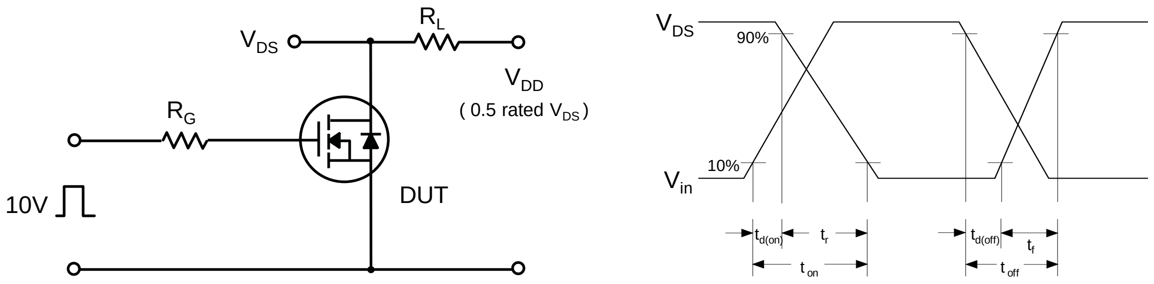


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

$$E_{AS} = \frac{1}{2} L_L I_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

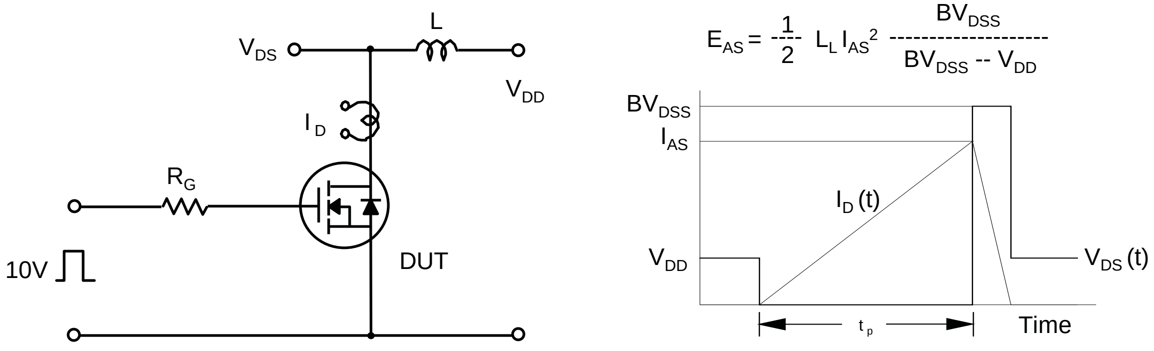
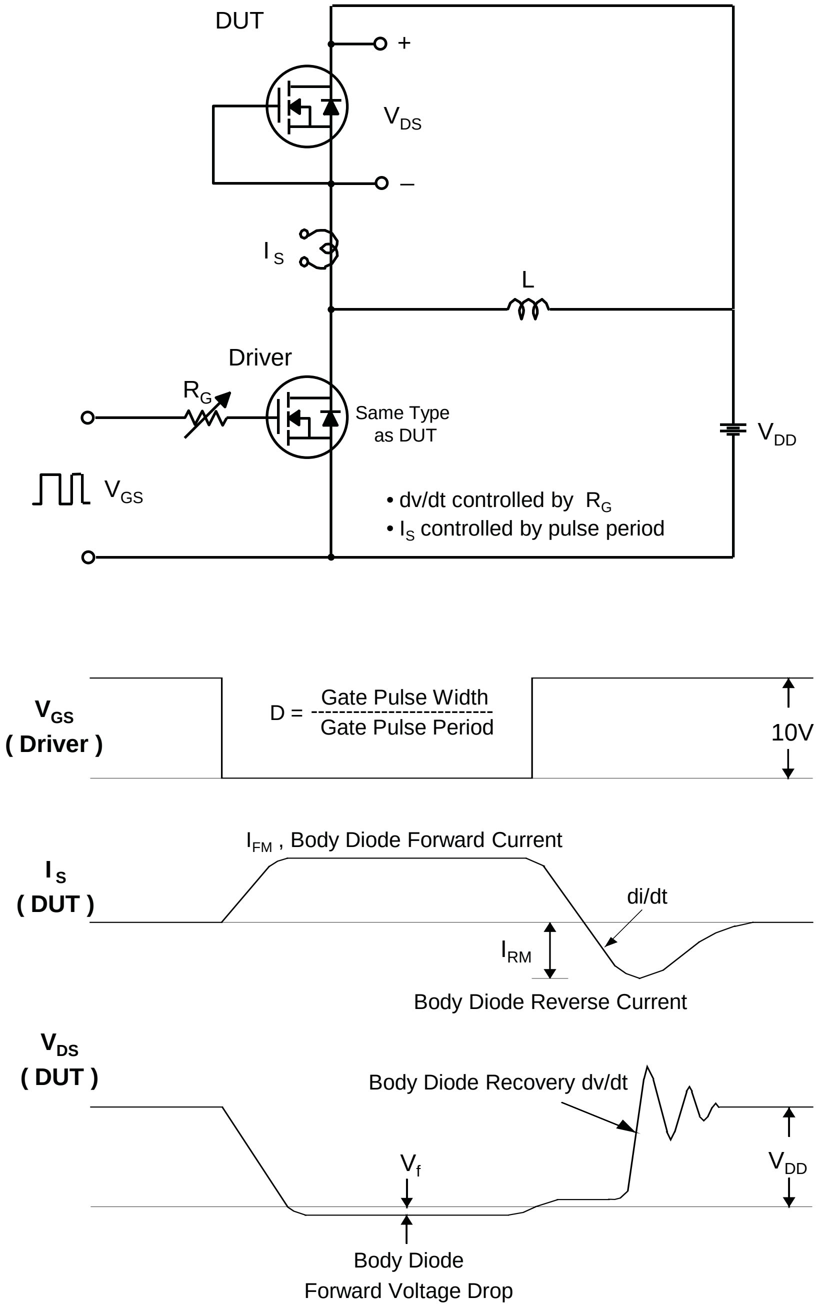
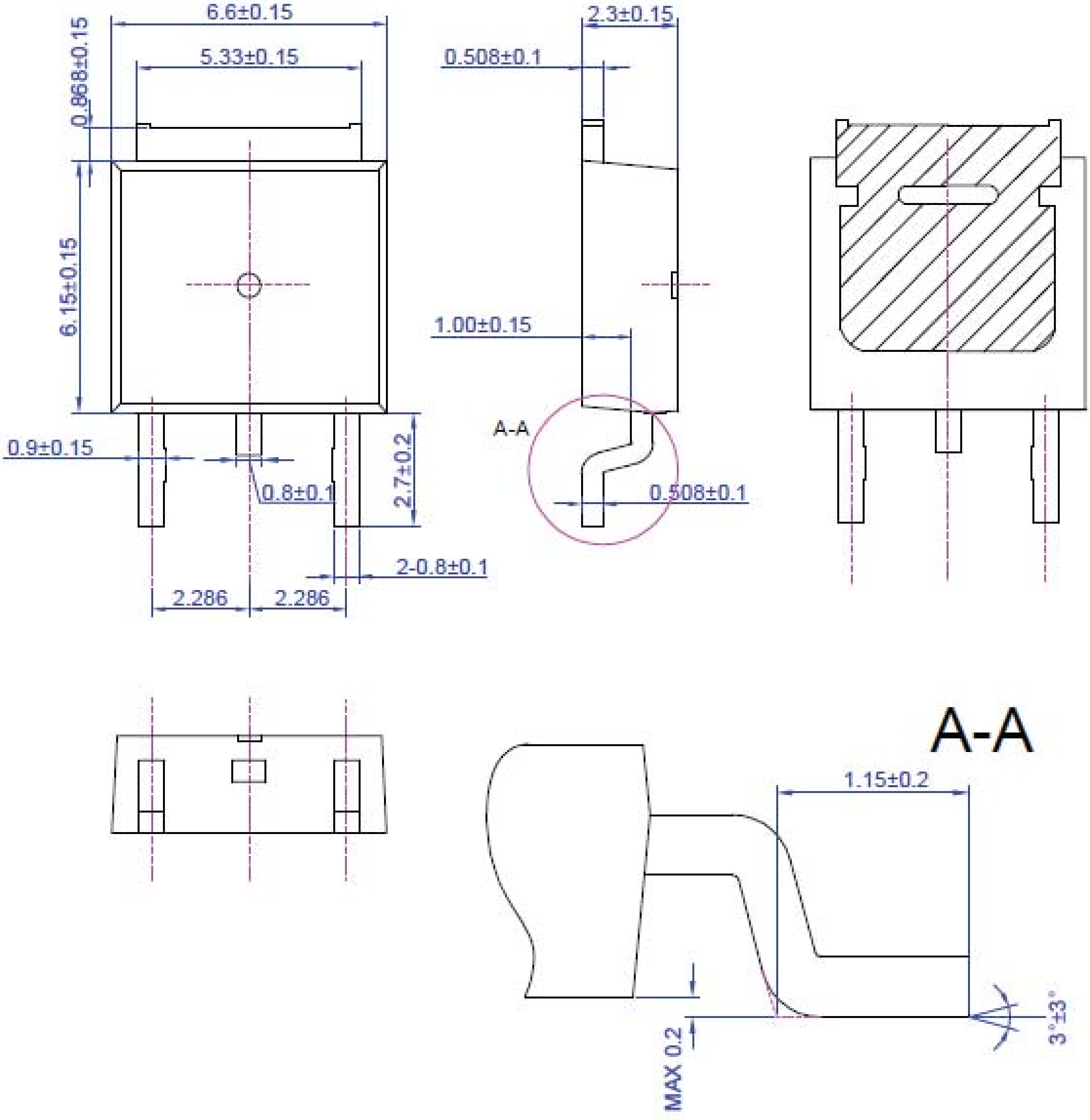


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimension

TO-252A
(D-PAK)



Package Dimension

TO-251A
(I-PAK)